

Hubert Gnaser

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Optimized Alkali-Metal Cationization in Secondary Ion Mass Spectrometry of Polyethylene Glycol Oligomers with up to m/z 10000: Dependence on Cation Species and Concentration. <i>Analytical Chemistry</i> , 2020, 92, 1511-1517.	6.5	2
2	Cationization and fragmentation of molecular ions sputtered from polyethylene glycol under gas cluster bombardment: An analysis by MS and MS/MS. <i>International Journal of Mass Spectrometry</i> , 2018, 430, 149-157.	1.5	5
3	Location and Electronic Nature of Phosphorus in the Si Nanocrystal $\hat{\sim}$ SiO ₂ System. <i>Scientific Reports</i> , 2015, 5, 9702.	3.3	61
4	Energy spectra of sputtered ions: assessment of the instrumental resolution. <i>Surface and Interface Analysis</i> , 2013, 45, 79-82.	1.8	4
5	Sputtered ion emission under size-selected Ar ⁿ⁺ cluster ion bombardment. <i>Surface and Interface Analysis</i> , 2013, 45, 138-142.	1.8	21
6	Peptide dissociation patterns in secondary ion mass spectrometry under large argon cluster ion bombardment. <i>Rapid Communications in Mass Spectrometry</i> , 2013, 27, 1490-1496.	1.5	18
7	Strongly reduced fragmentation and soft emission processes in sputtered ion formation from amino acid films under large Ar ⁿ⁺ ($\hat{\sim}$ 2200) cluster ion bombardment. <i>Rapid Communications in Mass Spectrometry</i> , 2012, 26, 1-8.	1.5	45
8	Temperature-dependent grain growth and phase transformation in mixed anatase-rutile nanocrystalline TiO ₂ films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 1635-1640.	1.8	8
9	Focused ion beam implantation of Ga in InP studied by SIMS and dynamic computer simulations. <i>Surface and Interface Analysis</i> , 2011, 43, 28-31.	1.8	5
10	Sputtered molecular fluoride anions: HfF ⁿ⁺ and WF ⁿ⁺ . <i>Surface and Interface Analysis</i> , 2011, 43, 32-35.	1.8	6
11	Nanostructures on surfaces by ion irradiation. <i>Pure and Applied Chemistry</i> , 2011, 83, 2003-2025.	1.9	9
12	Dynamic computer simulations of Cs incorporation in Si during low-energy (0.2-3 keV) irradiation. <i>Surface and Interface Analysis</i> , 2008, 40, 1367-1373.	1.8	6
13	Focused ion beam implantation of Ga in Si and Ge: fluence-dependent retention and surface morphology. <i>Surface and Interface Analysis</i> , 2008, 40, 1415-1422.	1.8	44